

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	18031	((semiconductor or wafer or substrate) near epitaxial)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/07 07:39
S2	10	((semiconductor or wafer or substrate) near epitaxial) and "FET" and "InGaP" and "n-type" and temperature and mobility and electron and space\$3 and channel and "MOCVD"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/20 14:11
S3	189	epitaxial near9 (substrate or semiconductor or wafer) and "FET" and ("InGaAs" near9 channel)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/07 07:41
S4	41	epitaxial near9 (substrate or semiconductor or wafer) and "FET" and ("InGaAs" near9 channel) and "InGaP" and (electron near9 mobil\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/07 07:42
S5	25	epitaxial near9 (substrate or semiconductor or wafer) and "FET" and ("InGaAs" near9 channel) and "InGaP" and (electron near9 mobil\$4) and temperature	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/07 08:10
S6	33	epitaxial near9 (substrate or semiconductor or wafer) and "HEMT" and ("InGaAs" near9 channel) and "InGaP" and (electron near9 mobil\$4) and temperature	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/07 08:24
S7	14	epitaxial near9 (substrate or semiconductor or wafer) and "HEMT" and ("InGaAs" near9 channel) and "InGaP" and (electron near9 mobil\$4) and (room near4 temperature)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/07 08:24